



《风光欣》技术资料

S8550

PNP EPITAXIAL SILICON TRANSISTOR

1W OUTPUT AMPLIFIER OF PORTABLE

RADIOS IN CLASS

B PUSH-PULL OPERATION

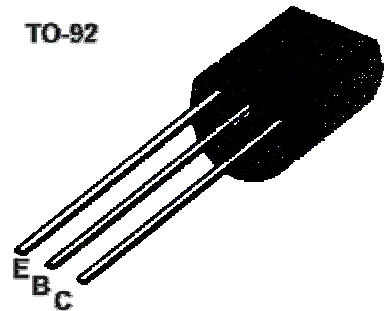
* Complimentary to **S8050**

* Collector Current $I_{cm} = 0.8A$

* Collector Dissipation: $P_c = 0.8W (T_c = 25)$

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-40	V
Collector-Emitter Voltage	V_{CE0}	-25	V
Emitter -Base Voltage	V_{EB0}	-6	V
Collector Current	I_c	-0.8	A
Collector Dissipation	P_c	0.8	W
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-65 ~ 150	



ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_c = -2mA, I_B = 0$	-25			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = -100 \mu A, I_c = 0$	-6			V
Collector Cut-off Current	I_{CB0}	$V_{CB} = -35V, I_E = 0$			-100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = -6V, I_c = 0$			-100	nA
DC Current Gain	H_{FE1}	$V_{CE} = -1V, I_c = -5mA$	45	170		
	H_{FE2}	$V_{CE} = -1V, I_c = -500mA$	85	160	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_c = -10mA$		-0.66	-1.0	V
Output Capacitance	C_{OB}	$f = 1MHz, V_{CB} = -10V, I_E = 0$		15		pF
Current Gain-Bandwidth Product	f_T	$V_{CE} = -10V, I_c = -50mA$	100	200		MHz

HFE(2) CLASSIFICATION

Classification	B	C	D	E	F
HFE(2)	85-160	120-200	160-300	300-400	400-500